



80V NPN DARLINGTON TRANSISTOR IN SOT223

Description

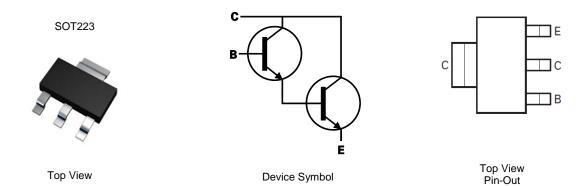
This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications

Features

- BV_{CEO} > 80V
- BV_{CBO} > 100V
- I_C = 2A High Continuous Current
- Useful hFE up to 6A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)



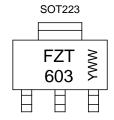
Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT603QTA	FZT603	7	12	1000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



FZT 603 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 8= 2018) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	10	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I _{CM}	6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0		
Dawar Dissipation	(Note 7)	Б	2.0	W	
Power Dissipation	(Note 8)	P _D	1.6	VV	
	(Note 9)		1.2	1	
	(Note 6)		41.7		
Thermal Decistores, lunction to Ambient	(Note 7)	<u> </u>	62.5		
Thermal Resistance, Junction to Ambient	(Note 8)	R _{OJA}	78.1	°C/W	
	(Note 9)		104		
Thermal Resistance Junction to Lead (Note 10)		$R_{\Theta JL}$	12.9		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 11)

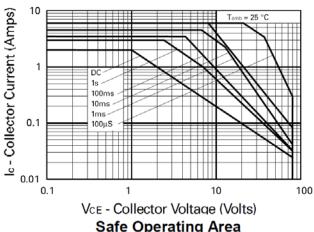
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	2000	V	2
Electrostatic Discharge—Machine Model	ESD MM	200	V	В

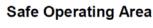
Notes:

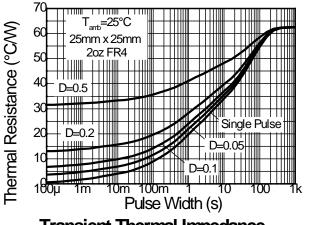
- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
- Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Same as Note 5, except the device is mounted on minimum recommended pad layout.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

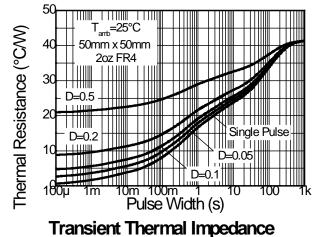


Thermal Characteristics and Derating Information

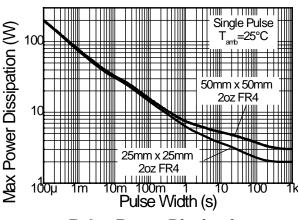


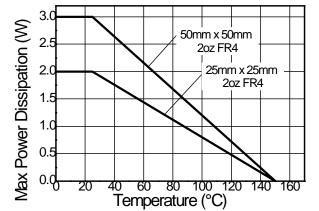






Transient Thermal Impedance





Pulse Power Dissipation

Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

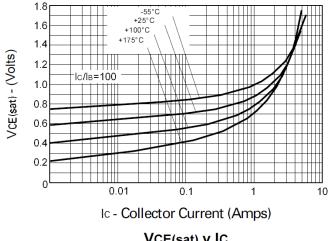
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	240	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	80	110	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	10	16	_	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	_	_	10 10	nΑ μΑ	V _{CB} = 80V V _{CB} = 80V, T _A = +100°C
Collector-Emitter Cut-Off Current	I _{CES}	_	_	10	μΑ	V _{CES} = 80V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 8V
DC Current Gain (Note 11)	hFE	3000 5000 3000 2000 —	14,000 15,000 14,000 10,000 2000 750	100,000 — — — —	ı	I _C = 50mA, V _{CE} = 5V I _C = 500mA, V _{CE} = 5V I _C = 1A, V _{CE} = 5V I _C = 2A, V _{CE} = 5V I _C = 5A, V _{CE} = 5V I _C = 6A, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}		0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13	V	$\begin{split} &I_{C}=250\text{mA},\ I_{B}=0.25\text{mA}\\ &I_{C}=0.4\text{A},\ I_{B}=0.4\text{mA}\\ &I_{C}=1\text{A},\ I_{B}=1\text{mA}\\ &I_{C}=2\text{A},\ I_{B}=20\text{mA}\\ &I_{C}=2\text{A},\ I_{B}=20\text{mA}, T_{J}=+150^{\circ}\text{C} \end{split}$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	1.70	1.95	V	$I_C = 2A$, $I_B = 20mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	1.50	1.75	V	$I_C = 2A, V_{CE} = 5V$
Input Capacitance (Note 11)	C _{ibo}	_	90	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance (Note 11)	C _{obo}	_	15	_	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 11)	f _T	150			MHz	V _{CE} = 10V, I _C = 100mA, f=20MHz
Turn-On Time	t _{on}	_	0.5	_	μs	V _{CC} = 10V, I _C = 500mA
Turn-Off Time	t _{off}	_	1.6	_	μs	$I_{B1} = -I_{B2} = 0.5 \text{mA}$

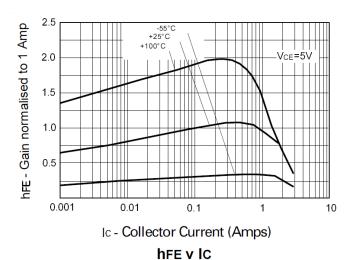
Note:

12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

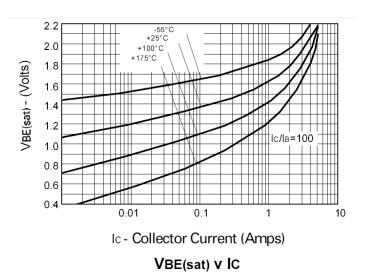


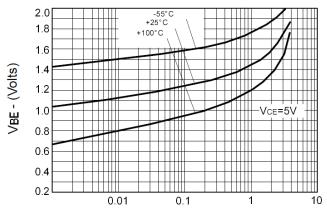
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





VCE(sat) v IC





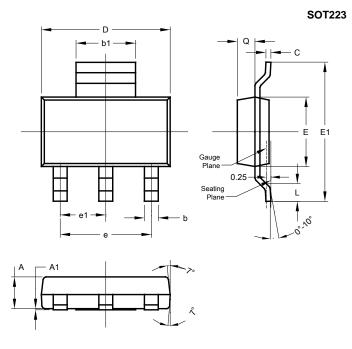
Ic - Collector Current (Amps)

VBE(on) v IC



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

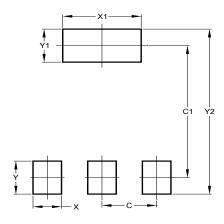


SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	_	_	4.60	
e1			2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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